**TENTATIVE** 

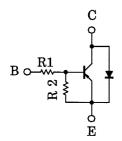
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

## **RN2357**

# Driver Circuit, Inverter Circuit, and Switching Applications

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- RN2307 and a diode are included in a SC-70 package.

### **Equivalent Circuit (Top View)**



#### **Bias Resistor Values**

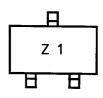
R1 (kΩ)	R2 (kΩ)
10	47

# 

### **Maximum Ratings (Ta = 25°C)**

Characterisstic	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	-50	V
Collector-emitter voltage	$V_{CEO}$	-50	V
Emitter-base voltage	V <sub>EBO</sub>	-6	V
Collector current	I <sub>C</sub>	-100	mA
Collector power dissipation	PC	100	mW
Junction temperature	Tj	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

#### Marking



### Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	_	$V_{CB} = -50V$ , $I_E = 0$	_	_	-0.1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	_	$V_{EB} = -6V, I_C = 0$	-	-	-0.2	mA
DC current gain	h <sub>FE</sub>	_	$V_{CE} = -5V, I_{C} = -10mA$	80	_	_	_
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	_	$I_C = -5mA$ , $I_B = -0.25mA$	_	-0.1	-0.3	V
Input voltage (ON)	V <sub>I (ON)</sub>	_	$V_{CE} = -0.2V$ , $I_{C} = -5mA$	-0.7	_	-1.8	V
Input voltage (OFF)	V <sub>I (OFF)</sub>	_	$V_{CE} = -5V, I_{C} = -0.1mA$	-0.5	_	-1.0	V
Translation Frequency	f <sub>T</sub>	_	$V_{CE} = -10V, I_{C} = -5mA$	_	200	_	MHz
Collector output capacitance	C <sub>ob</sub>	_	V <sub>CB</sub> = -10V, I <sub>E</sub> = 0, f = 1MHz	_	3.5	_	pF
Input resistor	R1	_	_	7	10	13	kΩ
Resistor ratio	R1/R2	_	_	0.17	0.21	0.25	_
Forward voltage (damper diode)	V <sub>F</sub>	_	IF =100mA	_	0.98	1.20	V

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